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(71)Applicant : TRI CHEMICAL LABORATORY
INC

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(72)Inventor : MACHIDA HIDEAKI
HOSHINO ASAKO

(54) MATERIAL FOR FORMING HAFNIUM-BASED OXIDE FILM

(57)Abstract:

PROBLEM TO BE SOLVED: To efficiently provide a technique for forming a neat hafnium-based film.

SOLUTION: A compound which is expressed by a chemical formula $(R_1R_2N)_4Hf$ is used.

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